

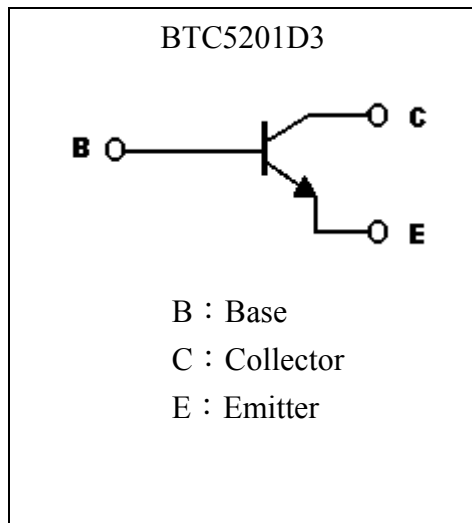
**Low Vcesat NPN Epitaxial Planar Transistor**

# BTC5201D3

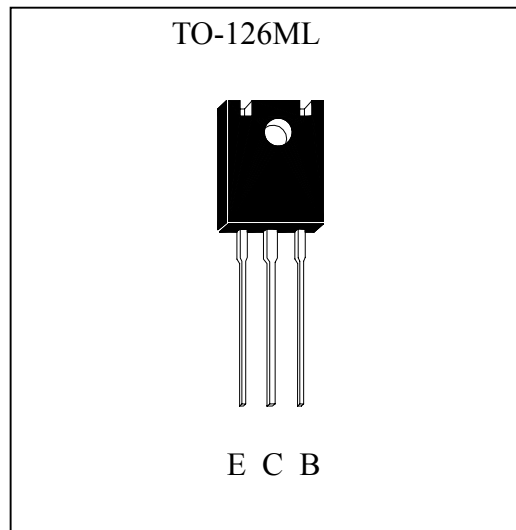
**Features**

- Low  $V_{CE(sat)}$
- High  $BV_{CEO}$
- Excellent current gain characteristics

**Symbol**



**Outline**



**Absolute Maximum Ratings** ( $T_a=25^{\circ}C$ )

| Parameter                               | Symbol          | Limits      | Unit          |
|-----------------------------------------|-----------------|-------------|---------------|
| Collector-Base Voltage                  | $V_{CBO}$       | 80          | V             |
| Collector-Emitter Voltage               | $V_{CEO}$       | 80          | V             |
| Emitter-Base Voltage                    | $V_{EBO}$       | 6           | V             |
| Collector Current (DC)                  | $I_C$           | 8           | A             |
| Collector Current (Pulse)               | $I_{CP}$        | 16 (Note 1) |               |
| Base Current                            | $I_B$           | 1           | A             |
| Power Dissipation @ $T_A=25^{\circ}C$   | $P_D$           | 1.5         | W             |
| Power Dissipation @ $T_C=25^{\circ}C$   | $P_D$           | 20          |               |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 83.3        | $^{\circ}C/W$ |
| Thermal Resistance, Junction to Case    | $R_{\theta JC}$ | 6.25        | $^{\circ}C/W$ |
| Junction Temperature                    | $T_j$           | 150         | $^{\circ}C$   |
| Storage Temperature                     | $T_{stg}$       | -55~+150    | $^{\circ}C$   |

Note : 1. Single Pulse ,  $P_w \leq 380\mu s, Duty \leq 2\%$ .

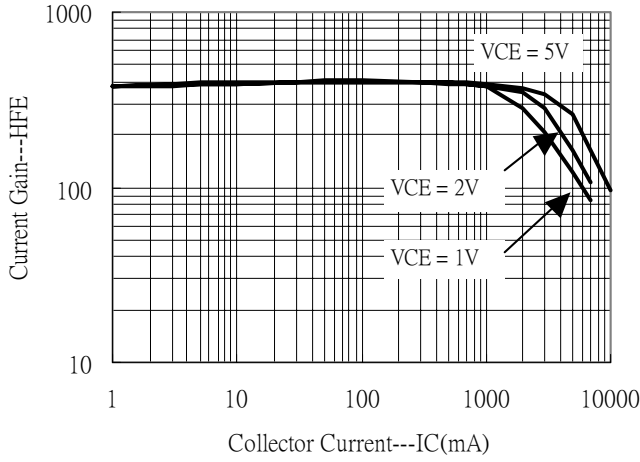
**Characteristics (Ta=25°C)**

| Symbol                  | Min. | Typ. | Max. | Unit | Test Conditions                                     |
|-------------------------|------|------|------|------|-----------------------------------------------------|
| BV <sub>CEO(SUS)</sub>  | 80   | -    | -    | V    | I <sub>C</sub> =30mA, I <sub>B</sub> =0             |
| I <sub>CES</sub>        | -    | -    | 10   | μA   | V <sub>CE</sub> =80V, V <sub>BE</sub> =0            |
| I <sub>EBO</sub>        | -    | -    | 50   | μA   | V <sub>EB</sub> =5V, I <sub>C</sub> =0              |
| *V <sub>CE(sat)</sub> 1 | -    | 0.1  | 0.3  | V    | I <sub>C</sub> =2A, I <sub>B</sub> =0.2A            |
| *V <sub>CE(sat)</sub> 2 | -    | -    | 0.6  | V    | I <sub>C</sub> =8A, I <sub>B</sub> =0.4A            |
| *V <sub>BE(sat)</sub> 1 | -    | -    | 1.2  | V    | I <sub>C</sub> =2A, I <sub>B</sub> =0.2A            |
| *V <sub>BE(sat)</sub> 2 | -    | -    | 1.5  | V    | I <sub>C</sub> =8A, I <sub>B</sub> =0.8A            |
| *h <sub>FE</sub> 1      | 60   | -    | -    | -    | V <sub>CE</sub> =1V, I <sub>C</sub> =0.1A           |
| *h <sub>FE</sub> 2      | 40   | -    | -    | -    | V <sub>CE</sub> =1V, I <sub>C</sub> =4A             |
| f <sub>T</sub>          | -    | 50   | -    | MHz  | V <sub>CE</sub> =6V, I <sub>C</sub> =500mA, f=20MHz |
| C <sub>ob</sub>         | -    | 130  | -    | pF   | V <sub>CB</sub> =10V, f=1MHz                        |

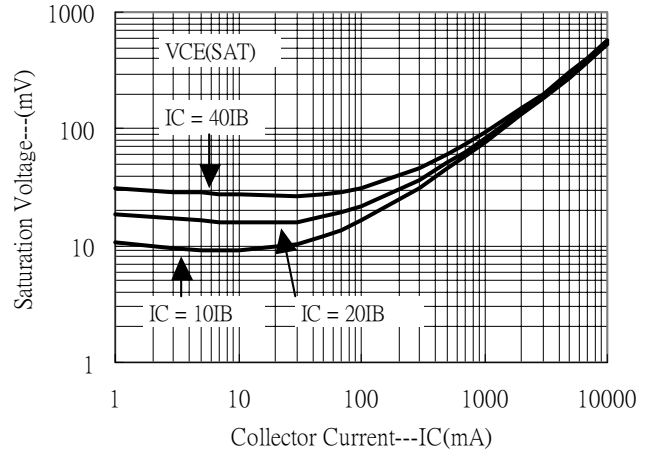
\*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

**Characteristic Curves**

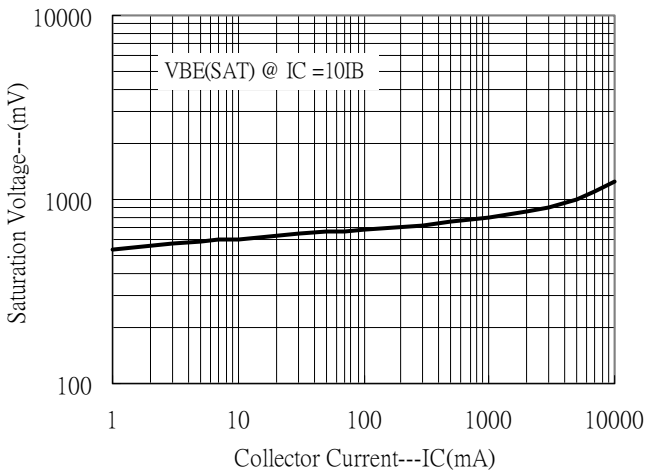
Current Gain vs Collector Current



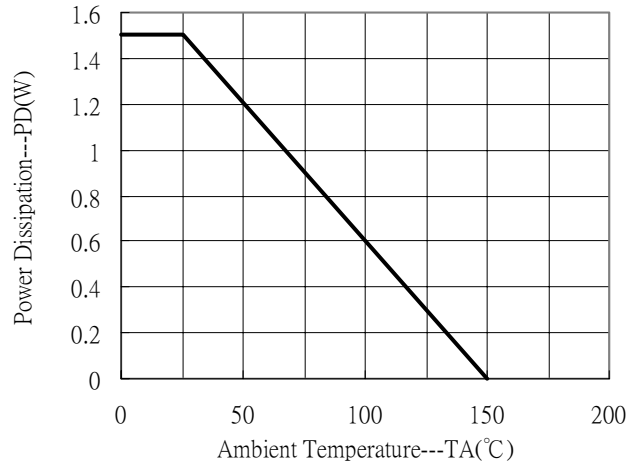
Saturation Voltage vs Collector Current



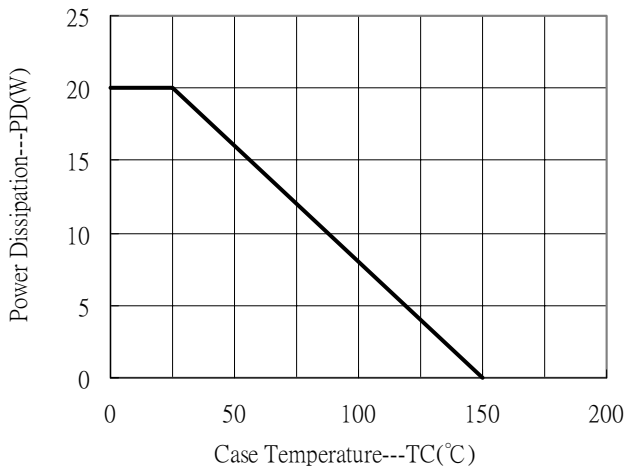
Saturation Voltage vs Collector Current



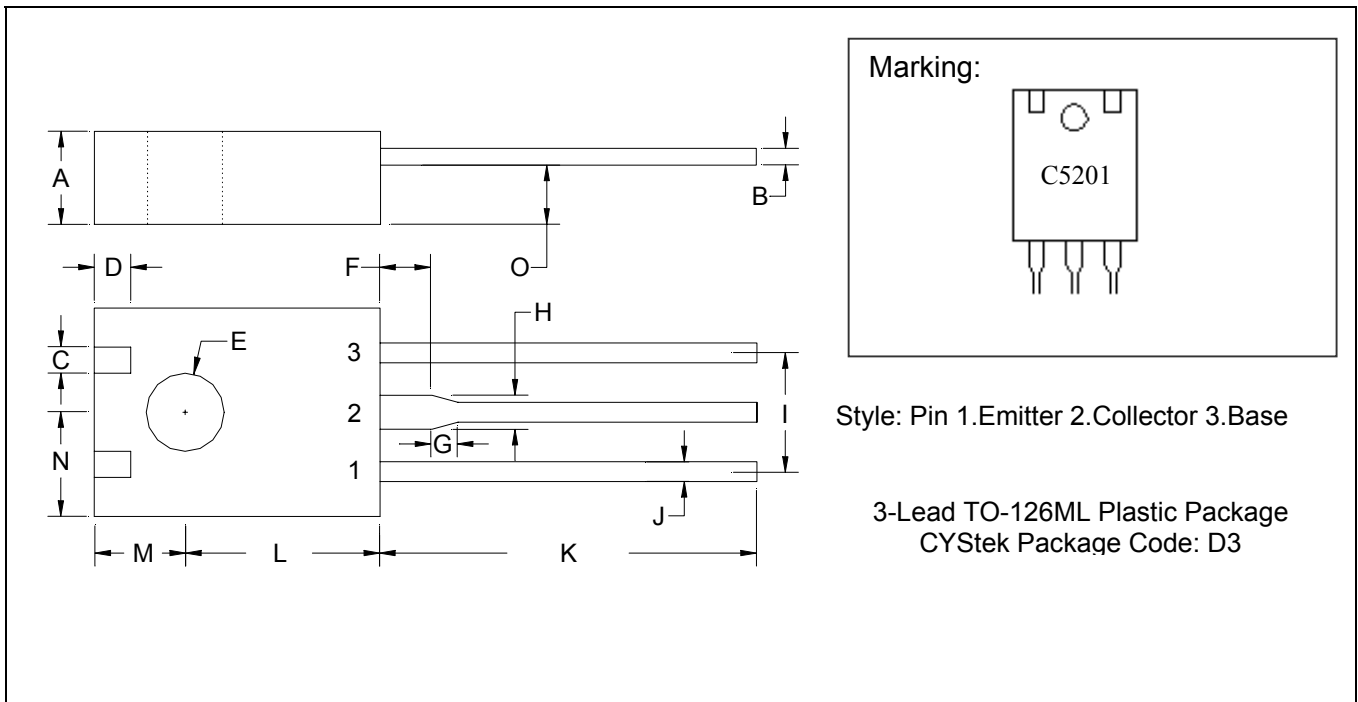
Power Derating Curve



Power Derating Curve



**TO-126ML Dimension**



\*: Typical

| DIM | Inches |        | Millimeters |      | DIM | Inches |         | Millimeters |       |
|-----|--------|--------|-------------|------|-----|--------|---------|-------------|-------|
|     | Min.   | Max.   | Min.        | Max. |     | Min.   | Max.    | Min.        | Max.  |
| A   | 0.1356 | 0.1457 | 3.44        | 3.70 | I   | -      | *0.1795 | -           | *4.56 |
| B   | 0.0170 | 0.0272 | 0.43        | 0.69 | J   | 0.0268 | 0.0331  | 0.68        | 0.84  |
| C   | 0.0344 | 0.0444 | 0.87        | 1.12 | K   | 0.5512 | 0.5906  | 14.00       | 15.00 |
| D   | 0.0501 | 0.0601 | 1.27        | 1.52 | L   | 0.2903 | 0.3003  | 7.37        | 7.62  |
| E   | 0.1131 | 0.1231 | 2.87        | 3.12 | M   | 0.1378 | 0.1478  | 3.50        | 3.75  |
| F   | 0.0737 | 0.0837 | 1.87        | 2.12 | N   | 0.1525 | 0.1625  | 3.87        | 4.12  |
| G   | 0.0294 | 0.0494 | 0.74        | 1.25 | O   | 0.0740 | 0.0842  | 1.88        | 2.14  |
| H   | 0.0462 | 0.0562 | 1.17        | 1.42 |     |        |         |             |       |

- Notes:**
- Controlling dimension: millimeters.
  - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
  - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: 42 Alloy ; solder plating
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

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